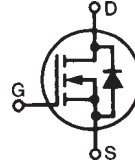


**TrenchT2™ HiperFET™**  
**Power MOSFET**

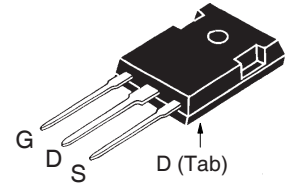
**IXFH320N10T2**  
**IXFT320N10T2**

$V_{DSS} = 100V$   
 $I_{D25} = 320A$   
 $R_{DS(on)} \leq 3.5m\Omega$

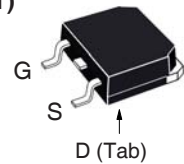
N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode



TO-247 (IXFH)



TO-268 (IXFT)



G = Gate      D = Drain  
S = Source     Tab = Drain

| Symbol     | Test Conditions  | Maximum Ratings |            |
|------------|--|-----------------|------------|
| $V_{DSS}$  | $T_J = 25^\circ C$ to $175^\circ C$                                | 100             | V          |
| $V_{DGR}$  | $T_J = 25^\circ C$ to $175^\circ C$ , $R_{GS} = 1M\Omega$          | 100             | V          |
| $V_{GSS}$  | Continuous   | $\pm 20$        | V          |
| $V_{GSM}$  | Transient  | $\pm 30$        | V          |
| $I_{D25}$  | $T_C = 25^\circ C$ (Chip Capability)                               | 320             | A          |
| $I_{LRMS}$ | Lead Current Limit, RMS  | 160             | A          |
| $I_{DM}$   | $T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$               | 800             | A          |
| $I_A$      | $T_C = 25^\circ C$   | 160             | A          |
| $E_{AS}$   | $T_C = 25^\circ C$   | 1.5             | J          |
| dv/dt      | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 175^\circ C$ | 15              | V/ns       |
| $P_D$      | $T_C = 25^\circ C$   | 1000            | W          |
| $T_J$      |  | -55 ... +175    | $^\circ C$ |
| $T_{JM}$   |  | 175             | $^\circ C$ |
| $T_{stg}$  |  | -55 ... +175    | $^\circ C$ |
| $T_L$      | 1.6mm (0.062in.) from Case for 10s                                 | 300             | $^\circ C$ |
| $T_{sold}$ | Plastic Body for 10 seconds  | 260             | $^\circ C$ |
| $M_d$      | Mounting Torque (TO-247)   | 1.13 / 10       | Nm/lb.in.  |
| Weight     | TO-247   | 6               | g          |
|            | TO-268   | 4               | g          |

| Symbol       | Test Conditions   | Characteristic Values |      |               |
|--------------|---|-----------------------|------|---------------|
|              |   | Min.                  | Typ. | Max.          |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 1mA$                               | 100                   |      | V             |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 250\mu A$                      | 2.0                   |      | 4.0 V         |
| $I_{GSS}$    | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$                        |                       |      | $\pm 200$ nA  |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$<br>$T_J = 150^\circ C$ |                       |      | 25 $\mu A$    |
|              |   |                       |      | 1.75 mA       |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 100A$ , Notes 1 & 2               |                       |      | 3.5 $m\Omega$ |

**Features**

- International Standard Packages
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Fast Intrinsic Diode
- Low  $R_{DS(on)}$

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- Synchronous Rectification
- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies
- High Speed Power Switching Applications

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)  | Characteristic Values |      |                        |
|--------------|--|-----------------------|------|------------------------|
|              |  | Min.                  | Typ. | Max.                   |
| $g_{fs}$     | $V_{DS} = 10\text{V}$ , $I_D = 60\text{A}$ , Note 1  | 80                    | 130  | S                      |
| $C_{iss}$    | $V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$   |                       | 26   | nF                     |
| $C_{oss}$    |  |                       | 2250 | pF                     |
| $C_{rss}$    |  |                       | 450  | pF                     |
| $R_{Gi}$     | Gate Input Resistance  |                       | 1.48 | $\Omega$               |
| $t_{d(on)}$  | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 100\text{A}$<br>$R_G = 1\Omega$ (External) |                       | 36   | ns                     |
| $t_r$        |  |                       | 46   | ns                     |
| $t_{d(off)}$ |  |                       | 73   | ns                     |
| $t_f$        |  |                       | 177  | ns                     |
| $Q_{g(on)}$  | $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$   |                       | 430  | nC                     |
| $Q_{gs}$     |  |                       | 110  | nC                     |
| $Q_{gd}$     |  |                       | 125  | nC                     |
| $R_{thJC}$   |  |                       |      | $0.15^\circ\text{C/W}$ |
| $R_{thCH}$   | TO-247   | 0.21                  |      | $^\circ\text{C/W}$     |

### Source-Drain Diode

| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)                            | Characteristic Values |      |        |
|----------|--|-----------------------|------|--------|
|          |  | Min.                  | Typ. | Max.   |
| $I_S$    | $V_{GS} = 0\text{V}$   |                       |      | 320 A  |
| $I_{SM}$ | Repetitive, Pulse Width Limited by $T_{JM}$  |                       |      | 1200 A |
| $V_{SD}$ | $I_F = 100\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1  |                       |      | 1.2 V  |
| $t_{rr}$ | $I_F = 150\text{A}$ , $V_{GS} = 0\text{V}$<br>$-di/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 50\text{V}$ |                       | 98   | ns     |
| $I_{RM}$ |  |                       | 6.6  | A      |
| $Q_{RM}$ |  |                       | 320  | nC     |

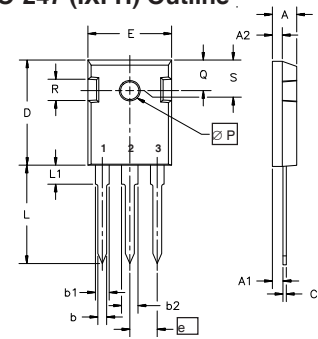
### Notes:

1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
2. Includes lead resistance.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2  
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

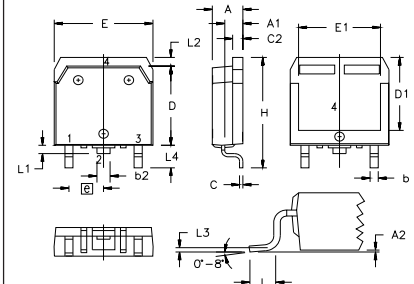
### TO-247 (IXFH) Outline



Terminals: 1 - Gate 2 - Drain  
3 - Source

| Dim.           | Millimeter |       | Inches  |       |
|----------------|------------|-------|---------|-------|
|                | Min.       | Max.  | Min.    | Max.  |
| A              | 4.7        | 5.3   | .185    | .209  |
| A <sub>1</sub> | 2.2        | 2.54  | .087    | .102  |
| A <sub>2</sub> | 2.2        | 2.6   | .059    | .098  |
| b              | 1.0        | 1.4   | .040    | .055  |
| b <sub>1</sub> | 1.65       | 2.13  | .065    | .084  |
| b <sub>2</sub> | 2.87       | 3.12  | .113    | .123  |
| C              | .4         | .8    | .016    | .031  |
| D              | 20.80      | 21.46 | .819    | .845  |
| E              | 15.75      | 16.26 | .610    | .640  |
| e              | 5.20       | 5.72  | 0.205   | 0.225 |
| L              | 19.81      | 20.32 | .780    | .800  |
| L1             |            | 4.50  |         | .177  |
| ∅P             | 3.55       | 3.65  | .140    | .144  |
| Q              | 5.89       | 6.40  | 0.232   | 0.252 |
| R              | 4.32       | 5.49  | .170    | .216  |
| S              |            |       | 242 BSC |       |

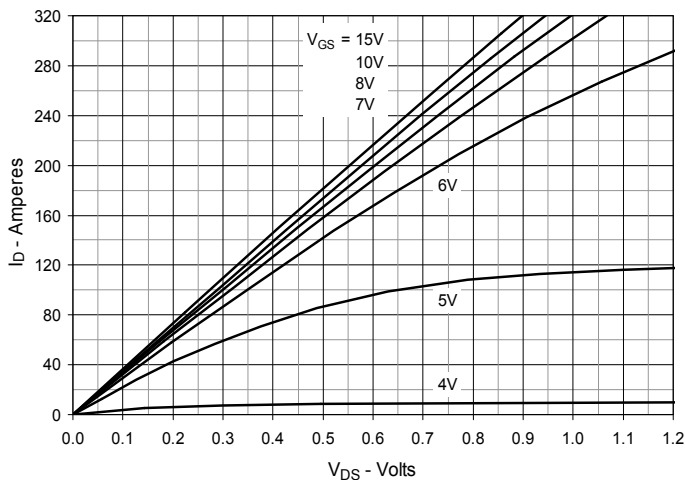
### TO-268 (IXFT) Outline



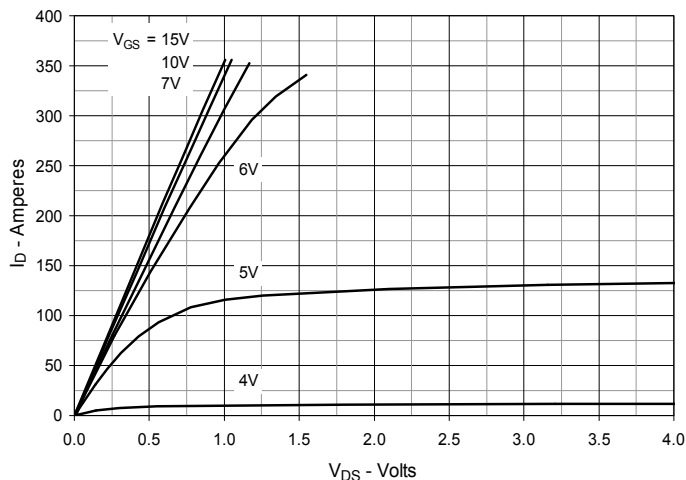
Terminals: 1 - Gate 2 - Drain  
3 - Source 4 - Drain

| SYM | INCHES   |      | MILLIMETERS |       |
|-----|----------|------|-------------|-------|
|     | MIN      | MAX  | MIN         | MAX   |
| A   | .193     | .201 | 4.90        | 5.10  |
| A1  | .106     | .114 | 2.70        | 2.90  |
| A2  | .001     | .010 | 0.02        | 0.25  |
| b   | .045     | .057 | 1.15        | 1.45  |
| b2  | .075     | .083 | 1.90        | 2.10  |
| C   | .016     | .026 | 0.40        | 0.65  |
| C2  | .057     | .063 | 1.45        | 1.60  |
| D   | .543     | .551 | 13.80       | 14.00 |
| D1  | .488     | .500 | 12.40       | 12.70 |
| E   | .624     | .632 | 15.85       | 16.05 |
| E1  | .524     | .535 | 13.30       | 13.60 |
| e   | .215 BSC |      | 5.45 BSC    |       |
| H   | .736     | .752 | 18.70       | 19.10 |
| L   | .094     | .106 | 2.40        | 2.70  |
| L1  | .047     | .055 | 1.20        | 1.40  |
| L2  | .039     | .045 | 1.00        | 1.15  |
| L3  | .010 BSC |      | 0.25 BSC    |       |
| L4  | .150     | .161 | 3.80        | 4.10  |

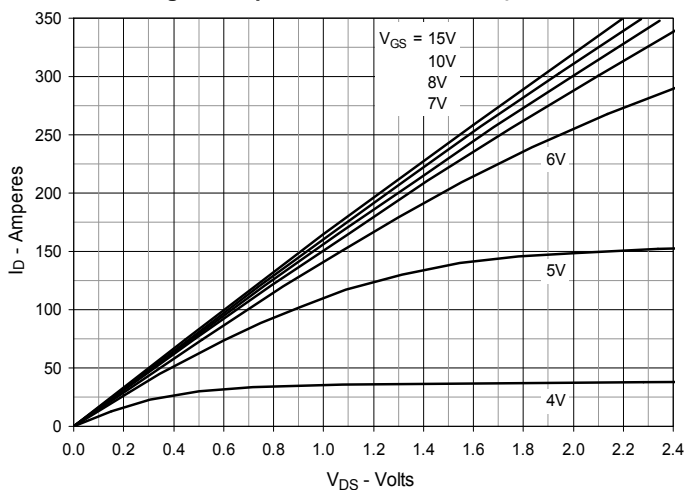
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



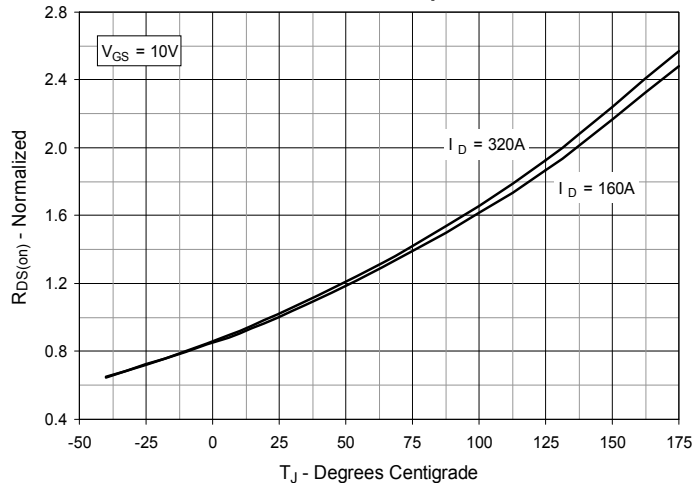
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



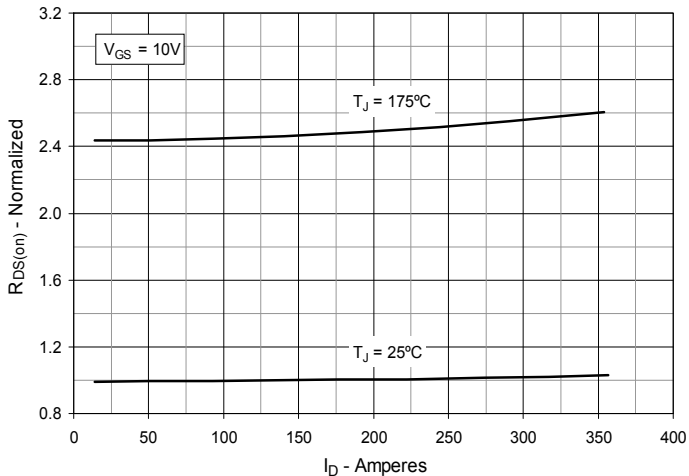
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



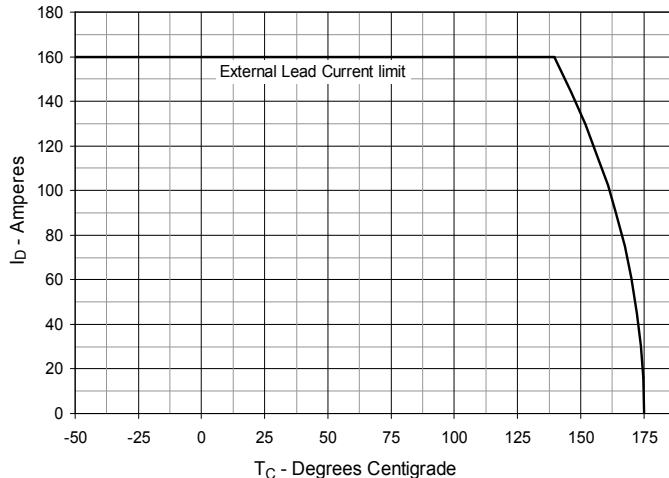
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 160\text{A}$  Value vs. Junction Temperature**



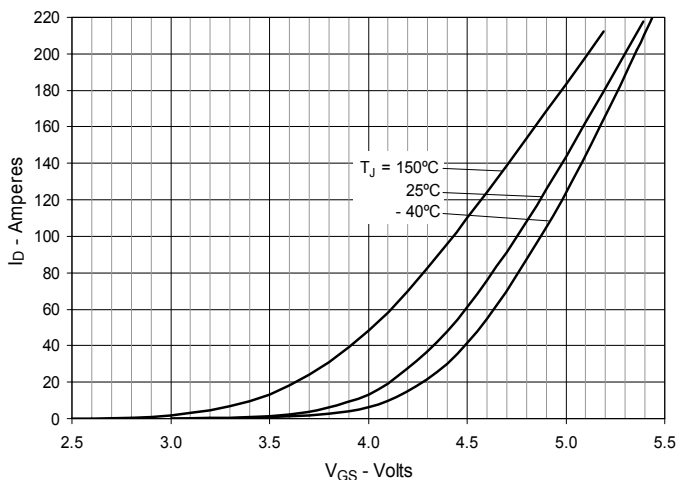
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 160\text{A}$  vs. Drain Current**



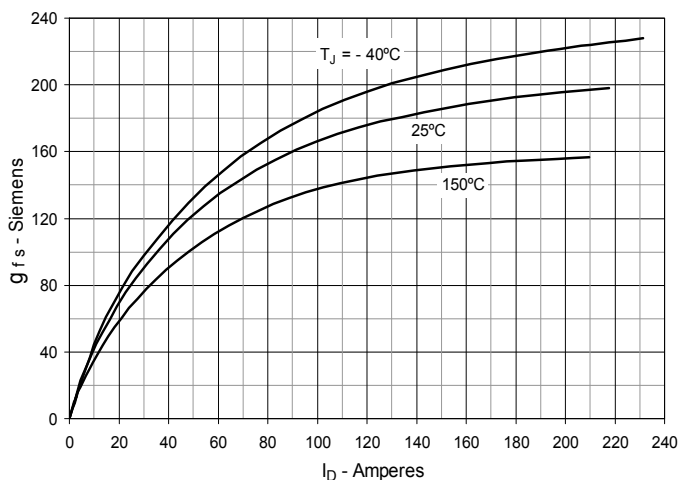
**Fig. 6. Drain Current vs. Case Temperature**



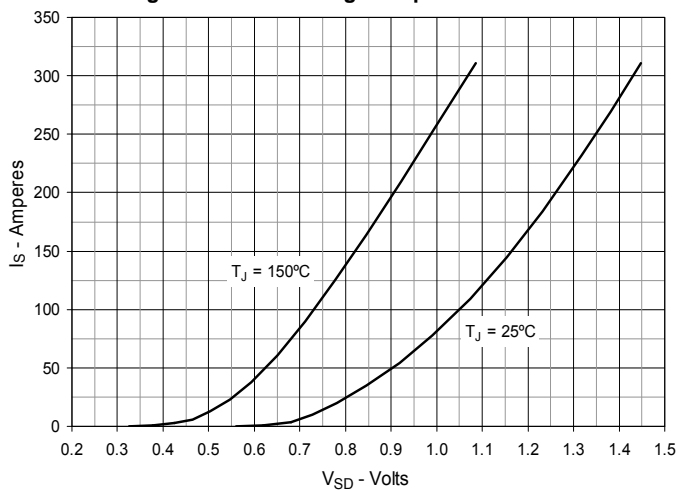
**Fig. 7. Input Admittance**



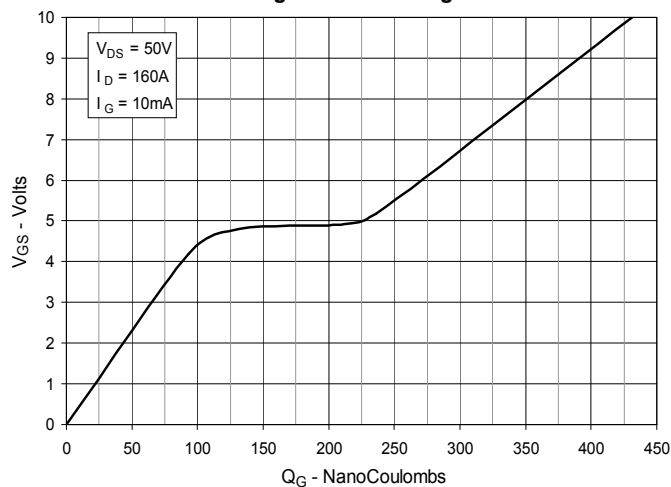
**Fig. 8. Transconductance**



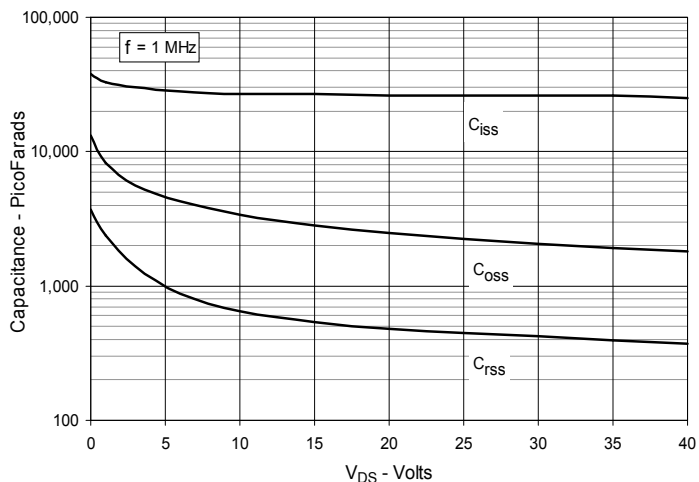
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



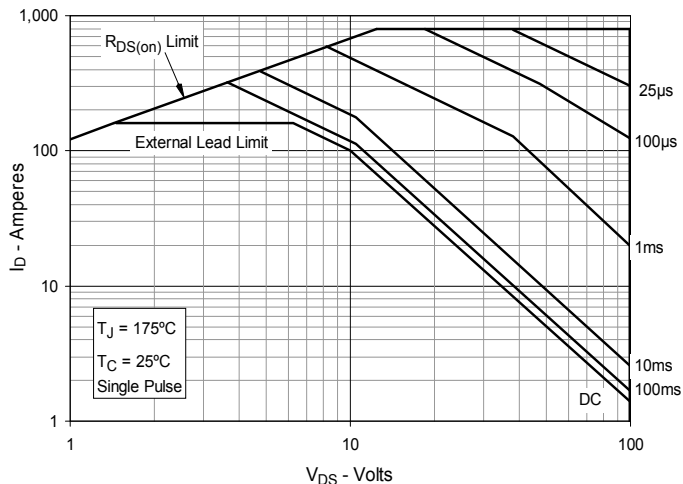
**Fig. 10. Gate Charge**



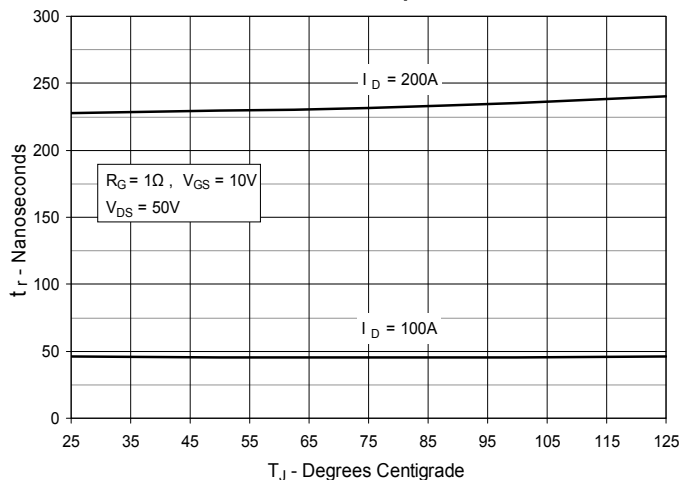
**Fig. 11. Capacitance**



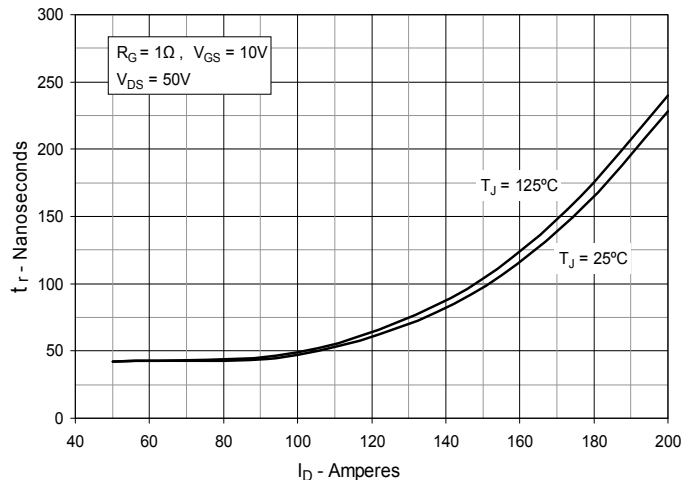
**Fig. 12. Forward-Bias Safe Operating Area**



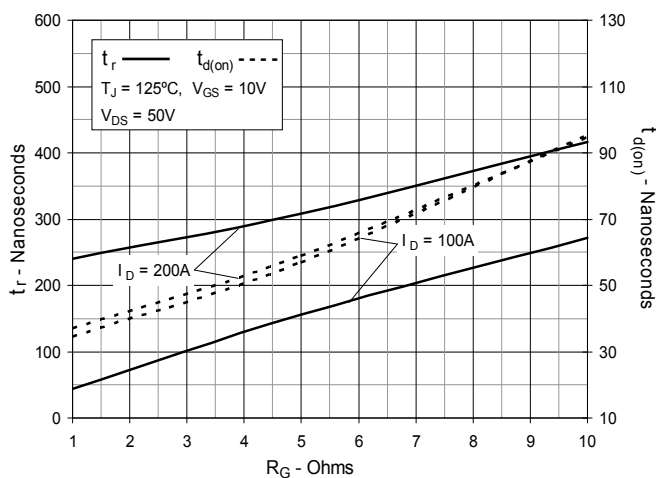
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



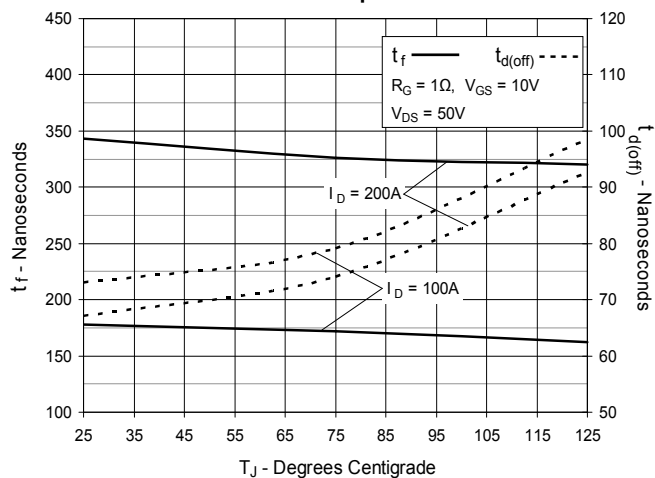
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



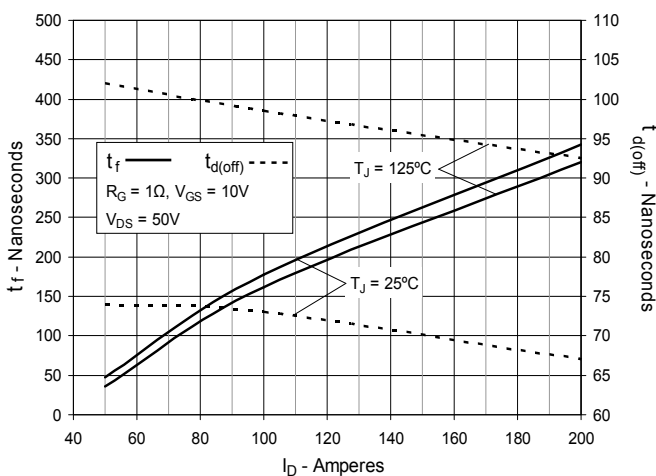
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

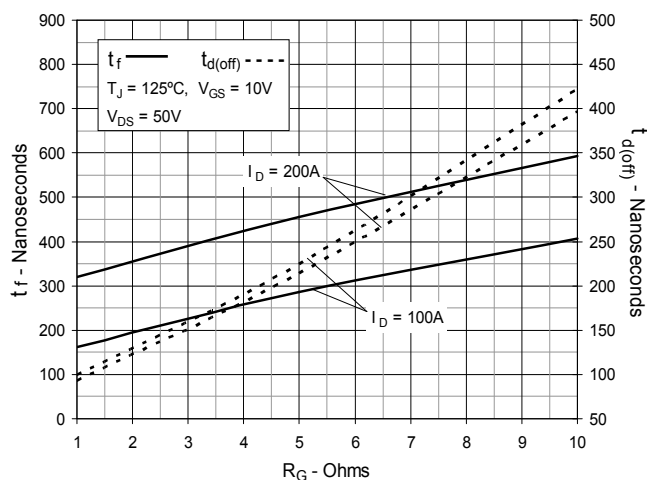
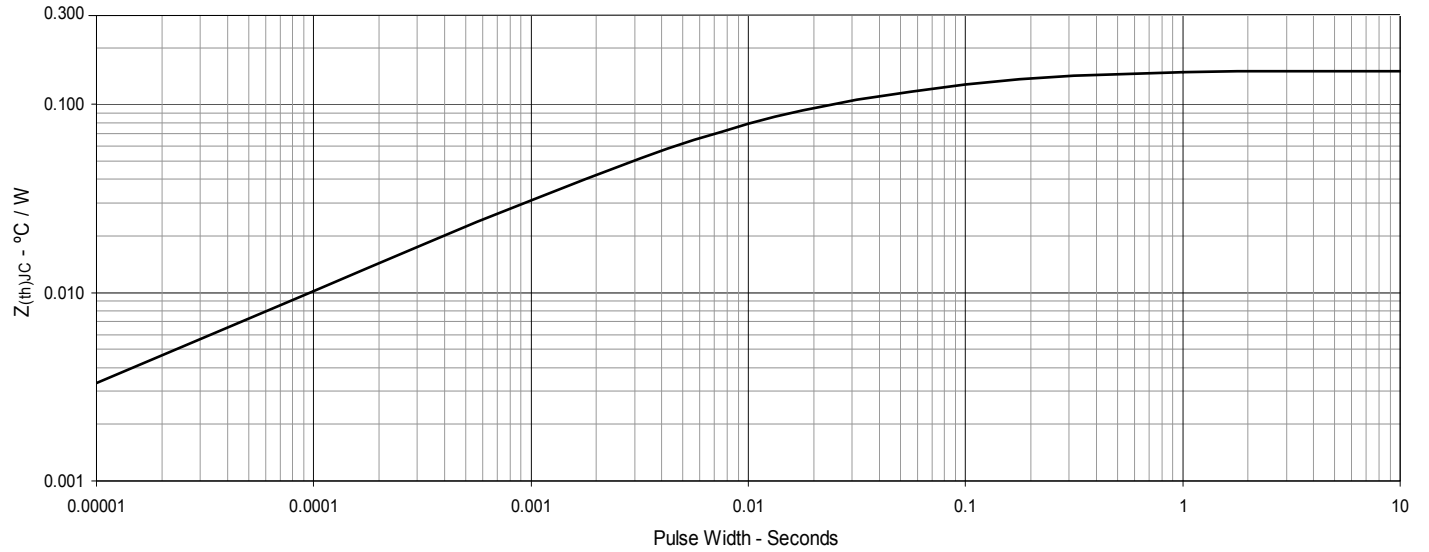


Fig. 19. Maximum Transient Thermal Impedance





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